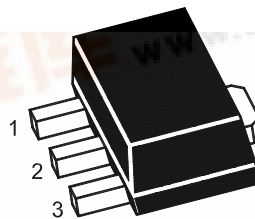


ST 2SD882U

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NPN Silicon Power Transistor

The transistor is subdivided into four groups, R, Q, P and E, according to its DC current gain.



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current	I_{C}	3	A
Collector Current (pulse)	$I_{\text{C}}(\text{pulse})$	7	A
Total power dissipation ($T_a = 25^\circ\text{C}$)	P_{tot}	1	W
Total power dissipation ($T_c = 25^\circ\text{C}$)	P_{tot}	10	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

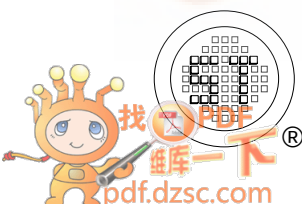
Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{\text{CE}} = 2\text{ V}$, $I_{\text{C}} = 1\text{ A}$					
Current Gain Group R	h_{FE}	60	-	120	-
Current Gain Group Q	h_{FE}	100	-	200	-
Current Gain Group P	h_{FE}	160	-	320	-
Current Gain Group E	h_{FE}	200	-	400	-
at $V_{\text{CE}} = 2\text{ V}$, $I_{\text{C}} = 20\text{ mA}$	h_{FE}	30	-	-	-
Collector Cutoff Current at $V_{\text{CB}} = 30\text{ V}$	I_{CBO}	-	-	1	μA
Emitter Cutoff Current at $V_{\text{EB}} = 3\text{ V}$	I_{EBO}	-	-	1	μA
Collector Emitter Saturation Voltage at $I_{\text{C}} = 2\text{ A}$, $I_{\text{B}} = 0.2\text{ A}$	$V_{\text{CE(sat)}}$	-	-	0.5	V
Base Emitter Saturation Voltage at $I_{\text{C}} = 2\text{ A}$, $I_{\text{B}} = 0.2\text{ A}$	$V_{\text{BE(sat)}}$	-	-	2	V
Gain Bandwidth Product at $V_{\text{CE}} = 5\text{ V}$, $I_{\text{C}} = 0.1\text{ A}$	f_{T}	-	90	-	MHz
Output Capacitance $V_{\text{CB}} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	45	-	pF

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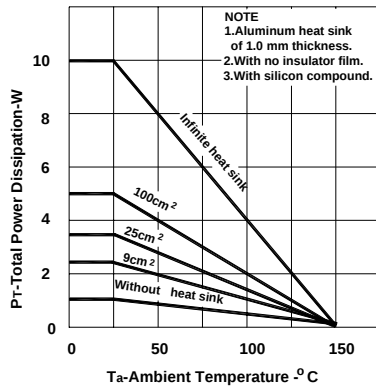
(Subsidiary of Sino-Tech International Holdings Limited, a company
listed on the Hong Kong Stock Exchange, Stock Code: 724)



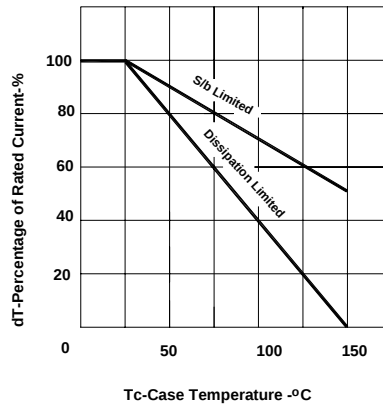
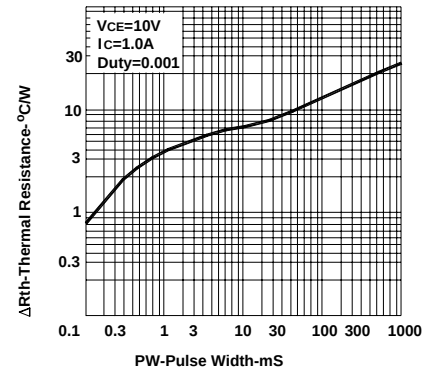
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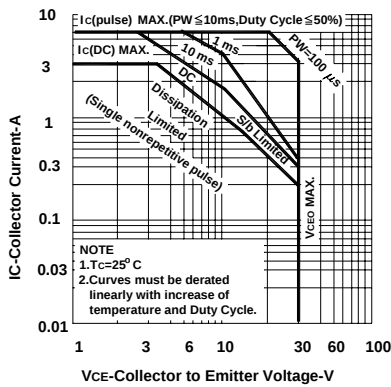
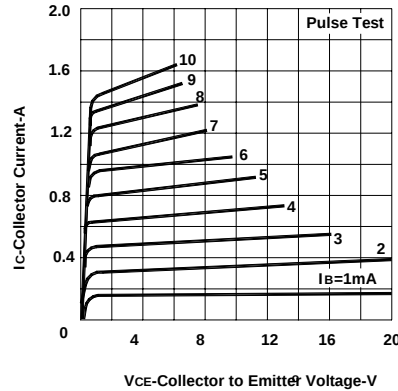
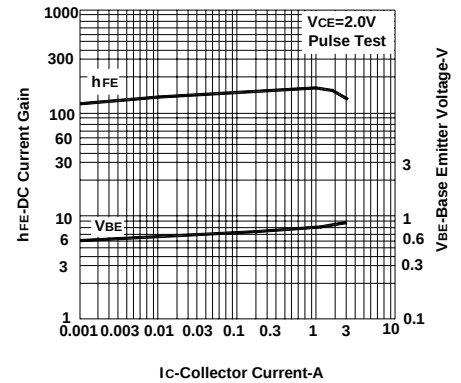
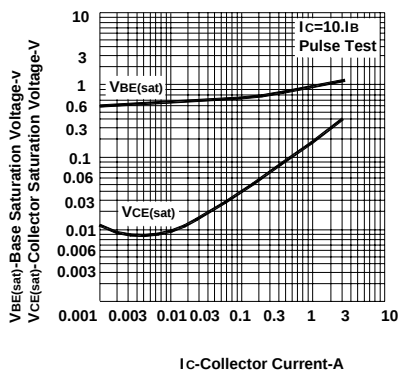
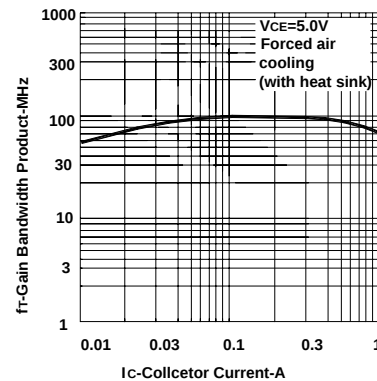
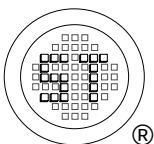
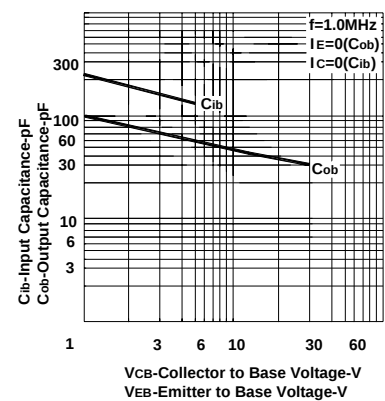
TYPICAL CHARACTERISTICS (Ta=25°C)

TOTAL POWER DISSIPATION vs.
AMBIENT TEMPERATURE

DERATING CURVES FOR ALL TYPES

THERMAL RESISTANCE vs.
PULSE WIDTH

SAFE OPERATING AREAS

COLLECTOR CURRENT vs.
COLLECTOR TO EMITTER VOLTAGEDC CURRENT GAIN, BASE TO EMITTER
VOLTAGE vs. COLLECTOR CURRENTBASE AND COLLECTOR SATURATION
VOLTAGE vs. COLLECTOR CURRENTGAIN BANDWIDTH PRODUCT vs.
COLLECTOR CURRENTINPUT AND OUTPUT CAPACITANCE vs.
REVERSE VOLTAGE

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ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001:2004
Certificate No. 71116



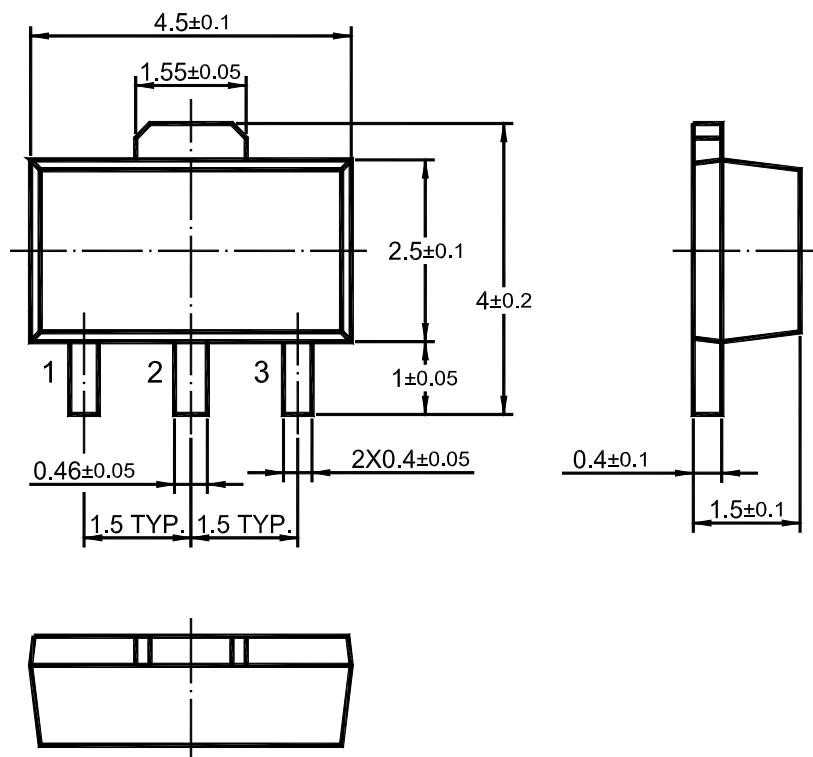
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Certificate No. 0506098

Dated : 22/03/2006

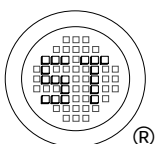
ST 2SD882U

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SOT-89 PACKAGE OUTLINE

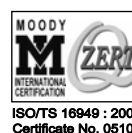


Dimensions in mm



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ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001:2004
Certificate No. 7116



ISO 9001:2000
Certificate No. 0506098

Dated : 22/03/2006